

## 2SB1204 / 2SD1804

PNP/NPN Epitaxial Planar Silicon Transistors

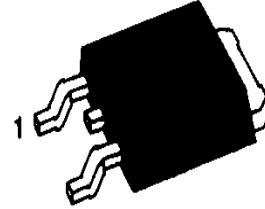
### Applications

- Relay drivers, high-speed inverters, converters, and other general high-current switching applications.

TO-252

### Features

- Low collector-to-emitter saturation voltage.
- High current and high  $f_T$ .
- Excellent linearity of  $h_{FE}$ .
- Fast switching time.
- Small and slim package making it easy to make 2SB1204/2SD1804-applied sets smaller.



1.Base 2.Collector 3.Emitter

### Specifications

#### Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	$V_{CBO}$		(-)60	V
Collector-to-Emitter Voltage	$V_{CEO}$		(-)50	V
Emitter-to-Base Voltage	$V_{EBO}$		(-)6	V
Collector Current	$I_C$		(-)8	A
Collector Current (Pulse)	$I_{CP}$		(-)12	A
Collector Dissipation	$P_C$		1	W
		$T_c=25^\circ\text{C}$	20	W
Junction Temperature	$T_j$		150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$		-55 to +150	$^\circ\text{C}$

#### Electrical Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	$I_{CBO}$	$V_{CB}=(-)40\text{V}, I_E=0$			(-)1	$\mu\text{A}$
Emitter Cutoff Current	$I_{EBO}$	$V_{EB}=(-)4\text{V}, I_C=0$			(-)1	$\mu\text{A}$
DC Current Gain	$h_{FE1}$	$V_{CE}=(-)2\text{V}, I_C=(-)0.5\text{A}$	70*		400*	
	$h_{FE2}$	$V_{CE}=(-)2\text{V}, I_C=(-)6\text{A}$	35			
Gain-Bandwidth Product	$f_T$	$V_{CE}=(-)5\text{V}, I_C=(-)1\text{A}$		(130)		MHz
				180		MHz
Output Capacitance	$C_{ob}$	$V_{CB}=(-)10\text{V}, f=1\text{MHz}$		(95)65		pF
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=(-)4\text{A}, I_B=(-)0.2\text{A}$		200	400	mV
				(-250)	(-500)	mV
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=(-)4\text{A}, I_B=(-)0.2\text{A}$		(-)0.95	(-)1.3	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=(-)10\mu\text{A}, I_E=0$	(-)60			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=(-)1\text{mA}, R_{BE}=\infty$	(-)50			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=(-)10\mu\text{A}, I_C=0$	(-)6			V
Turn-ON Time	$t_{on}$	See specified Test Circuit		(50)		ns
Storage Time	$t_{stg}$	See specified Test Circuit		(450)		ns
				500		ns
Fall Time	$t_f$	See specified Test Circuit		20		ns

\* : The 2SB1204/2SD1804 are classified by 0.5A  $h_{FE}$  as follows :

70	Q	140	100	R	200	140	S	280	200	T	400
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